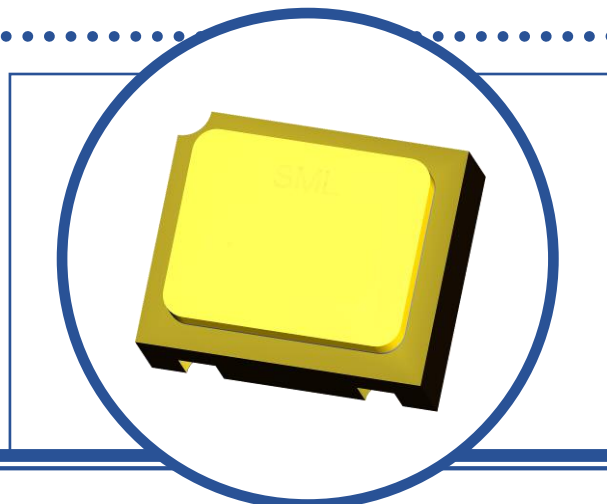


# SILICON SMALL SIGNAL N-CHANNEL JFET

## 2N4392CSM

- Hermetic Surface Mounted Package
- Designed For High Reliability and Space Applications
- Screening Options Available



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C unless otherwise stated)

|                  |  |                 |
|------------------|--|-----------------|
| V <sub>DS</sub>  | Drain – Source Voltage   | 40V             |
| V <sub>GS</sub>  | Gate – Source Voltage  | -40V            |
| V <sub>GD</sub>  | Gate – Drain Voltage   | -40V            |
| I <sub>G</sub>   | Gate Current   | 50mA            |
| P <sub>D</sub>   | Total Power Dissipation at T <sub>A</sub> = 25°C<br>De-rate Above 25°C | 300mW<br>2mW/°C |
| T <sub>J</sub>   | Junction Temperature Range   | -55 to +175°C   |
| T <sub>stg</sub> | Storage Temperature Range  | -65 to +200°C   |

### THERMAL PROPERTIES

| Symbols          | Parameters                              | Max. | Units |
|------------------|---|------|-------|
| R <sub>θJA</sub> | Thermal Resistance, Junction To Ambient | 500  | °C/W  |

Semelab Limited reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

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## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise stated)

| Symbols         | Parameters                      | Test Conditions                | Min.                      | Typ. | Max. | Units    |
|-----------------|---------------------------------|--------------------------------|---------------------------|------|------|----------|
| $V_{(BR)GSS}$   | Gate – Source Breakdown Voltage | $V_{DS} = 0V$ $I_G = 1.0\mu A$ | -40                       |      |      | V        |
| $V_{GS(off)}$   | Gate – Source Cut-off Voltage   | $V_{DS} = 20V$ $I_D = 1.0nA$   | -2                        |      | -5   |          |
| $I_{DSS}^{(1)}$ | Saturation Drain Current        | $V_{DS} = 20V$ $V_{GS} = 0V$   | 25                        |      | 75   | mA       |
| $I_{GSS}$       | Gate Reverse Current            | $V_{DS} = 0V$ $V_{GS} = -20V$  |                           |      | -100 | pA       |
|                 |                                 |                                | $T_A = 150^\circ\text{C}$ |      |      | -200     |
| $I_{D(off)}$    | Drain Cut-off Current           | $V_{DS} = 20V$ $V_{GS} = -7V$  |                           |      | 100  | pA       |
|                 |                                 |                                | $T_A = 150^\circ\text{C}$ |      |      | 200      |
| $V_{DS(on)}$    | Drain – Source On Voltage       | $V_{GS} = 0V$ $I_D = 6mA$      |                           |      | 0.4  | V        |
| $R_{DS(on)}$    | Drain – Source On Resistance    | $V_{GS} = 0$ $I_D = 1.0mA$     |                           |      | 60   | $\Omega$ |

## DYNAMIC CHARACTERISTICS

|              |  |                                 |                                      |  |  |    |          |
|--------------|--|---------------------------------|--------------------------------------|--|--|----|----------|
| $C_{iss}$    | Common – Source Input Capacitance            | $V_{DS} = 20V$<br>$f = 1.0MHz$  | $V_{GS} = 0V$                        |  |  | 26 | pF       |
| $C_{rss}$    | Common – Source Reverse Transfer Capacitance | $V_{DS} = 0V$<br>$f = 1.0MHz$   | $V_{GS} = -7V$                       |  |  | 5  |          |
| $R_{DS(on)}$ | Drain – Source On Resistance                 | $V_{GS} = 0$<br>$f = 1.0KHz$    | $I_D = 0A$                           |  |  | 60 | $\Omega$ |
| $t_r$        | Rise Time                                    | $V_{DD} = 10V$<br>$V_{GS} = 0V$ | $V_{GSX} = -7V$<br>$I_{D(on)} = 6mA$ |  |  | 5  | ns       |
| $t_{d(on)}$  | Turn-on Delay Time                           |                                 |                                      |  |  | 15 |          |
| $t_f$        | Fall Time                                    |                                 |                                      |  |  | 20 |          |
| $t_{d(off)}$ | Turn-off Delay Time                          |                                 |                                      |  |  | 35 |          |

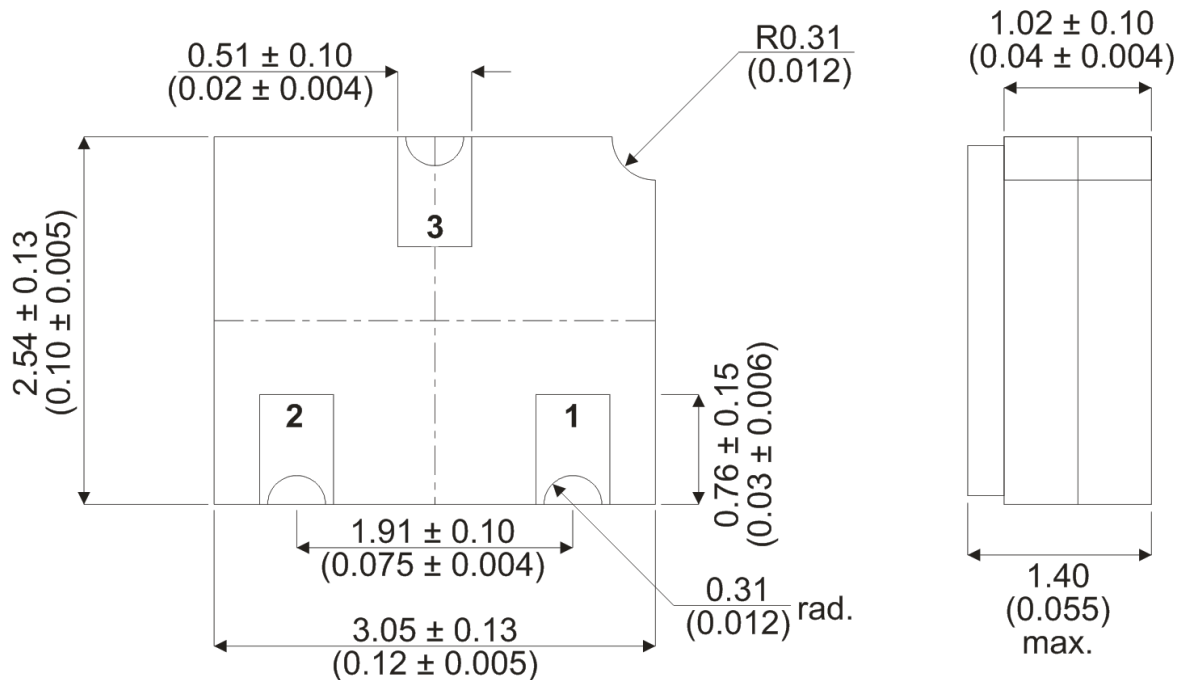
### Notes

(1) Pulse Width  $\leq 380\mu s$ ,  $\delta \leq 2\%$

# SILICON SMALL SIGNAL N-CHANNEL JFET 2N4392CSM

## MECHANICAL DATA

Dimensions in mm (inches)



**LCC1 (SOT23)  
Underside View**

| Pad 1  | Pad 2 | Pad 3 |
|--------|-------|-------|
| Source | Drain | Gate  |